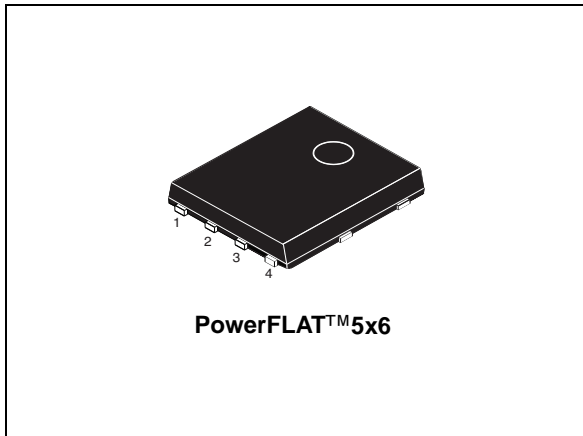


Automotive-grade N-channel 100 V, 0.008 Ω typ., 16 A STripFET™ F7 Power MOSFET in a PowerFLAT™ 5x6 package

Datasheet - production data

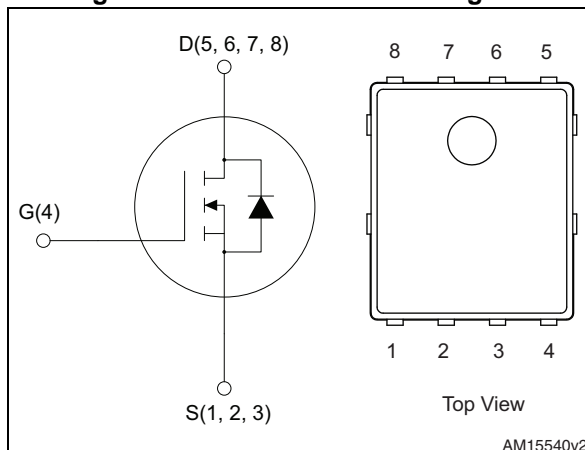


Features

Order code	V _{DS}	R _{DS(on) max}	I _D	P _{TOT}
STL92N10F7AG	100 V	0.0095 Ω	16 A	5 W

- Designed for automotive applications and AEC-Q101 qualified
- Among the lowest R_{DS(on)} on the market
- Excellent figure of merit (FoM)
- Low C_{rss}/C_{iss} ratio for EMI immunity
- High avalanche ruggedness
- Wettable flank package

Figure 1. Internal schematic diagram



Applications

- Switching applications

Description

This N-channel Power MOSFET utilizes STripFET™ F7 technology with an enhanced trench gate structure that results in very low on-state resistance, while also reducing internal capacitance and gate charge for faster and more efficient switching.

Table 1. Device summary

Order code	Marking	Package	Packaging
STL92N10F7AG	92N10F7	PowerFLAT™ 5x6	Tape and reel

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- 2 Electrical characteristics 4**
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- 3 Test circuits 8**
- 4 Package mechanical data 9**
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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	100	V
V_{GS}	Gate-source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	70	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	50	A
$I_D^{(2)}$	Drain current (continuous) at $T_{pcb} = 25\text{ }^\circ\text{C}$	16	A
$I_D^{(2)}$	Drain current (continuous) at $T_{pcb} = 100\text{ }^\circ\text{C}$	11	A
$I_{DM}^{(2)(3)}$	Drain current (pulsed)	64	A
$P_{TOT}^{(1)}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	100	W
$P_{TOT}^{(2)}$	Total dissipation at $T_{pcb} = 25\text{ }^\circ\text{C}$	5	W
T_{stg}	Storage temperature	-55 to 175 °C	°C
T_j	Operating junction temperature		

1. This value is rated according to R_{thj-c}
2. This value is rated according to $R_{thj-pcb}$
3. Pulse width limited by safe operating area.

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb max	31	°C/W
$R_{thj-case}$	Thermal resistance junction-case max	1.5	°C/W

1. When mounted on FR-4 board of 1 inch², 2 oz Cu.

2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified)

Table 4. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\ \mu\text{A}$, $V_{GS} = 0$	100			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = 100\ \text{V}$			1	μA
		$V_{DS} = 100\ \text{V}$, $T_C = 125\text{ °C}$			100	μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\ \text{V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{A}$	2.5	3.5	4.5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\ \text{V}$, $I_D = 8\ \text{A}$		0.008	0.0095	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 50\ \text{V}$, $f = 1\ \text{MHz}$, $V_{GS} = 0$	-	3100	-	pF
C_{oss}	Output capacitance		-	700	-	pF
C_{riss}	Reverse transfer capacitance		-	45	-	pF
Q_g	Total gate charge	$V_{DD} = 50\ \text{V}$, $I_D = 16\ \text{A}$, $V_{GS} = 10\ \text{V}$ (see Figure 14)	-	45	-	nC
Q_{gs}	Gate-source charge		-	18	-	nC
Q_{gd}	Gate-drain charge		-	13	-	nC

Table 6. Switching times

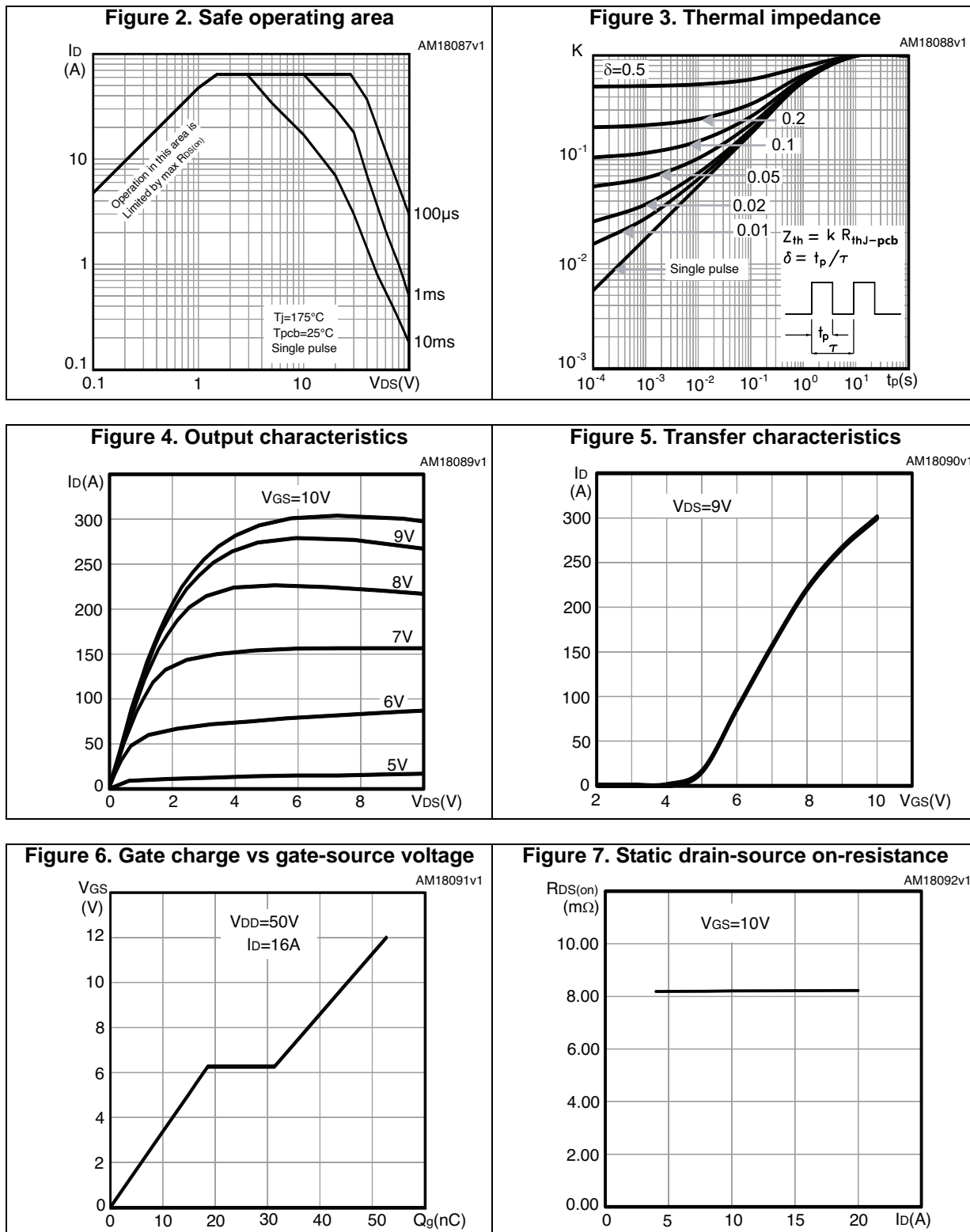
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 50\ \text{V}$, $I_D = 8\ \text{A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\ \text{V}$ (see Figure 15 and Figure 18)	-	19	-	ns
t_r	Rise time		-	32	-	ns
$t_{d(off)}$	Turn-off delay time		-	36	-	ns
t_f	Fall time		-	13	-	ns

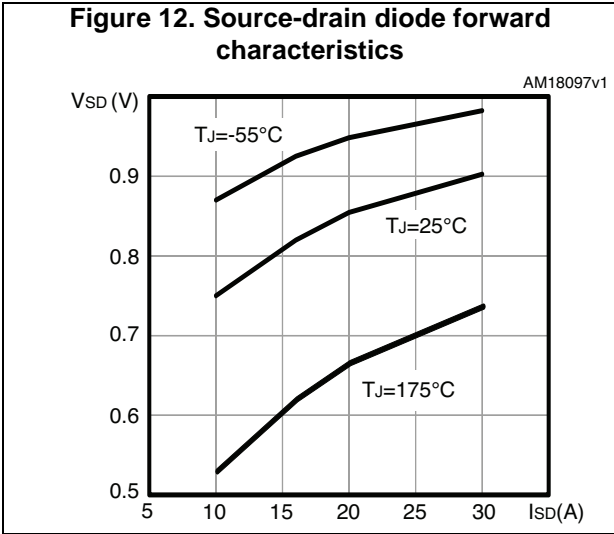
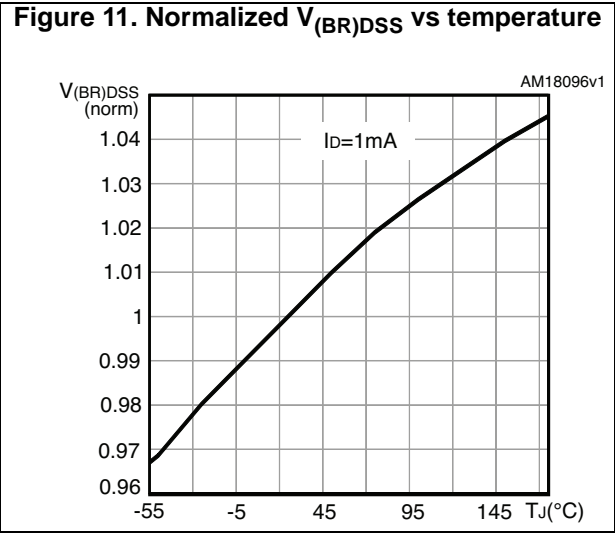
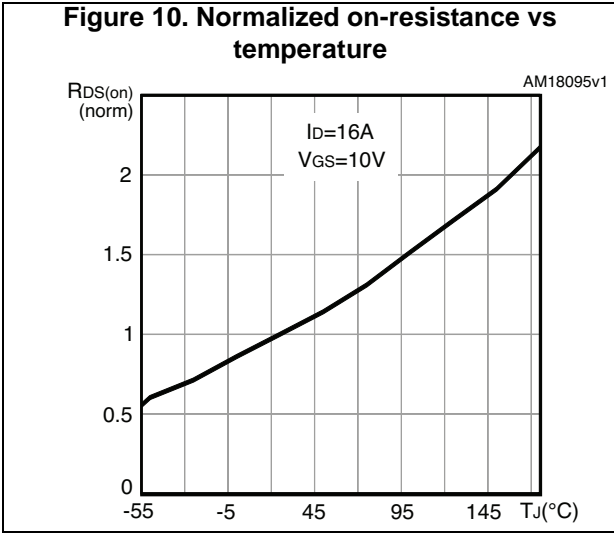
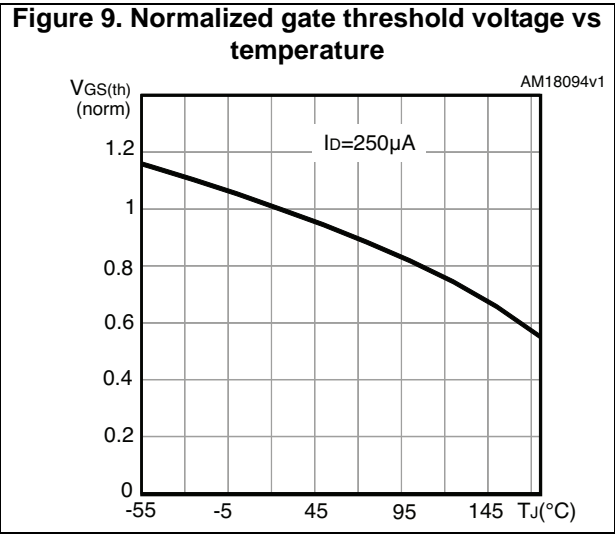
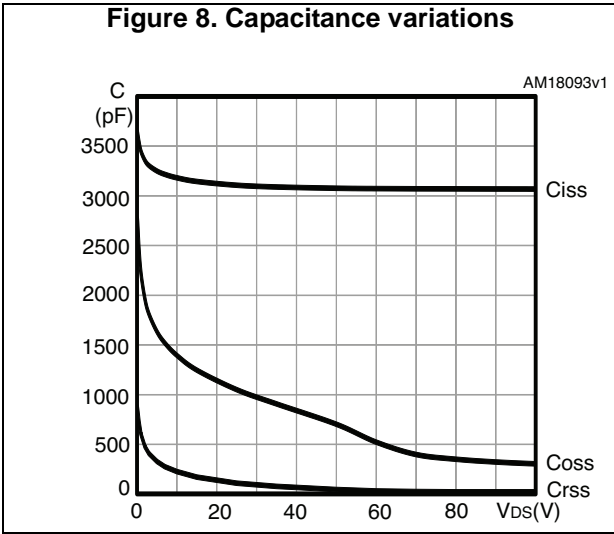
Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		16	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		64	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 16\text{ A}$, $V_{GS} = 0$	-		1.1	V
t_{rr}	Reverse recovery time	$I_{SD} = 16\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$	-	70		ns
Q_{rr}	Reverse recovery charge	$V_{DD} = 80\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 18)	-	125		nC
I_{RRM}	Reverse recovery current		-	3.6		A

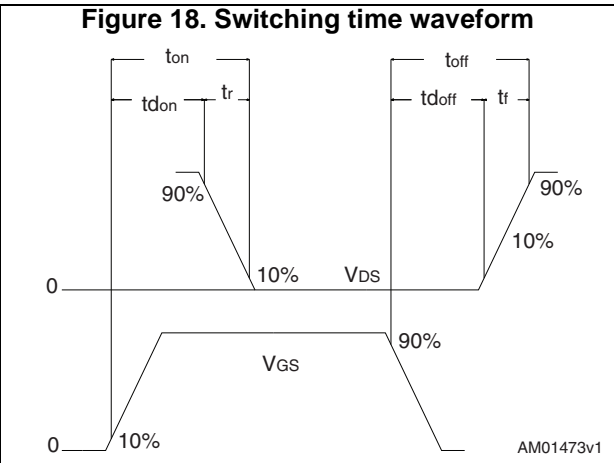
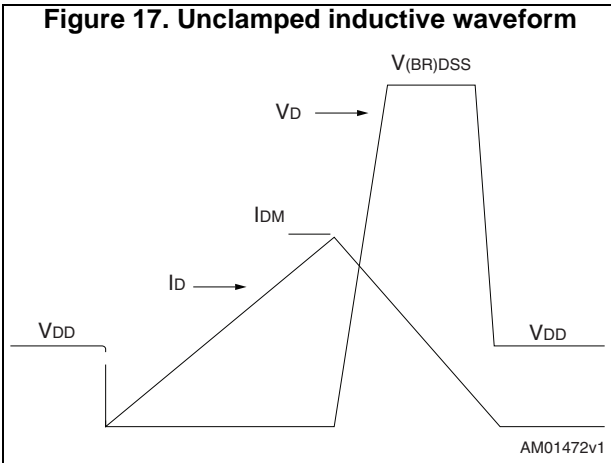
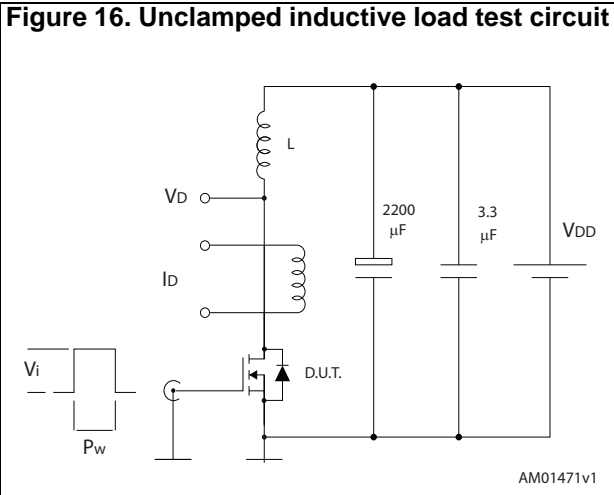
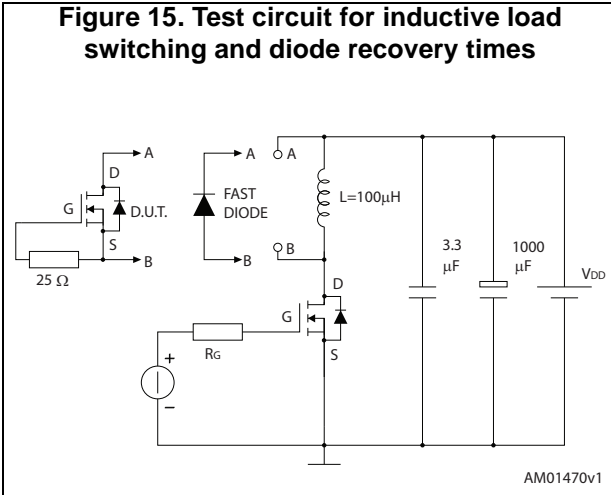
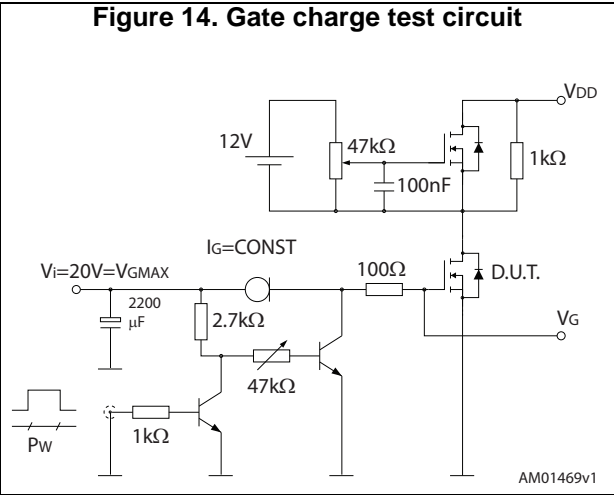
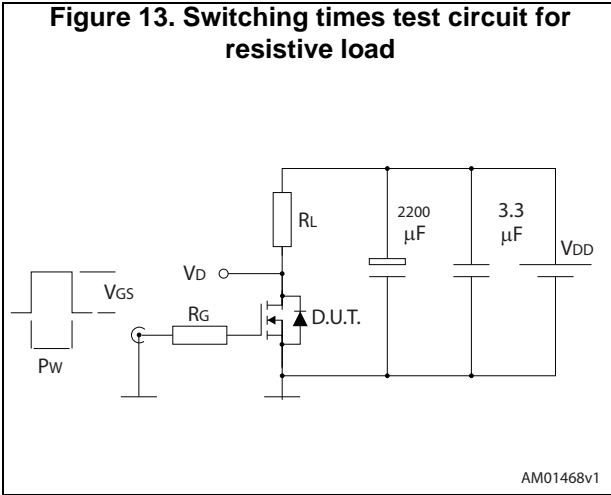
1. Pulse width limited by safe operating area.
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)





3 Test circuits



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

4.1 PowerFLAT™ 5x6 WF type R package information

Figure 19. PowerFLAT™ 5x6 WF type R package outline

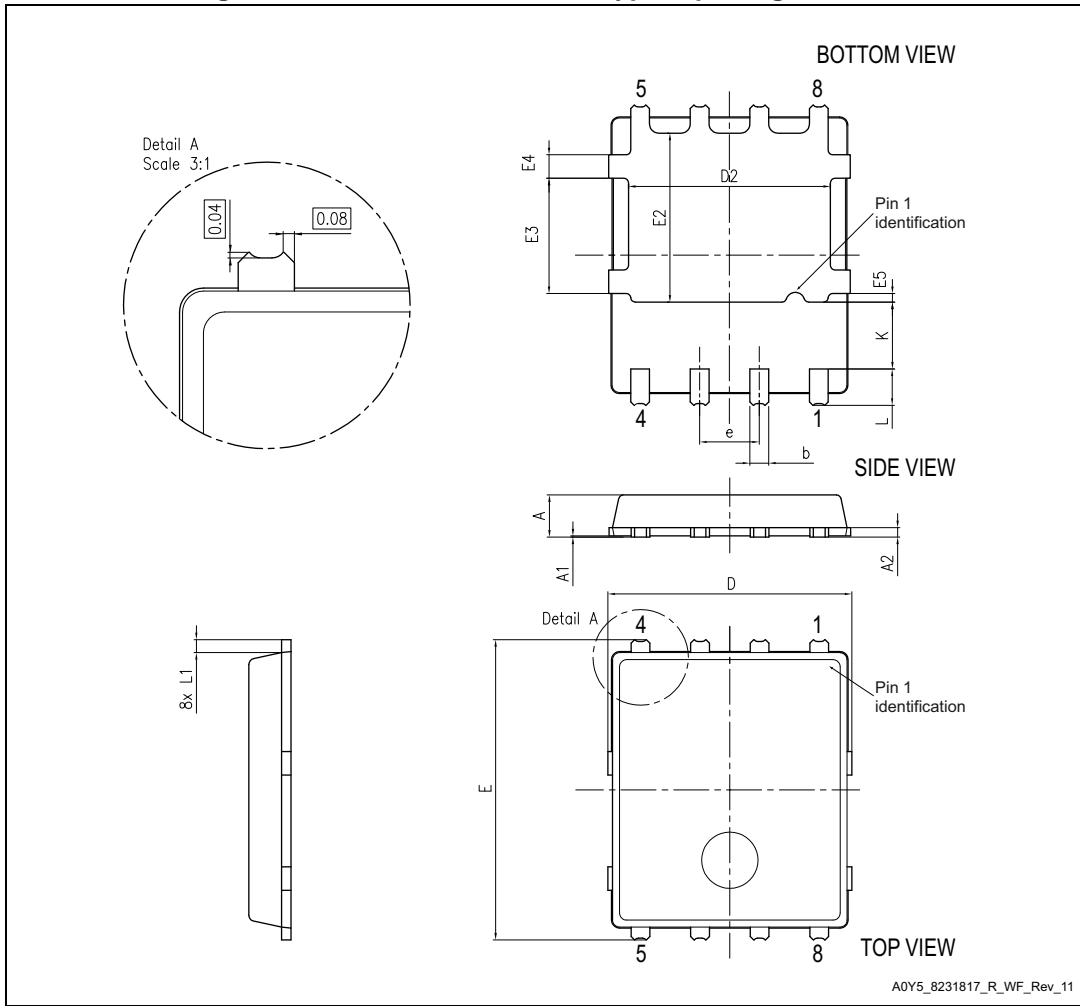
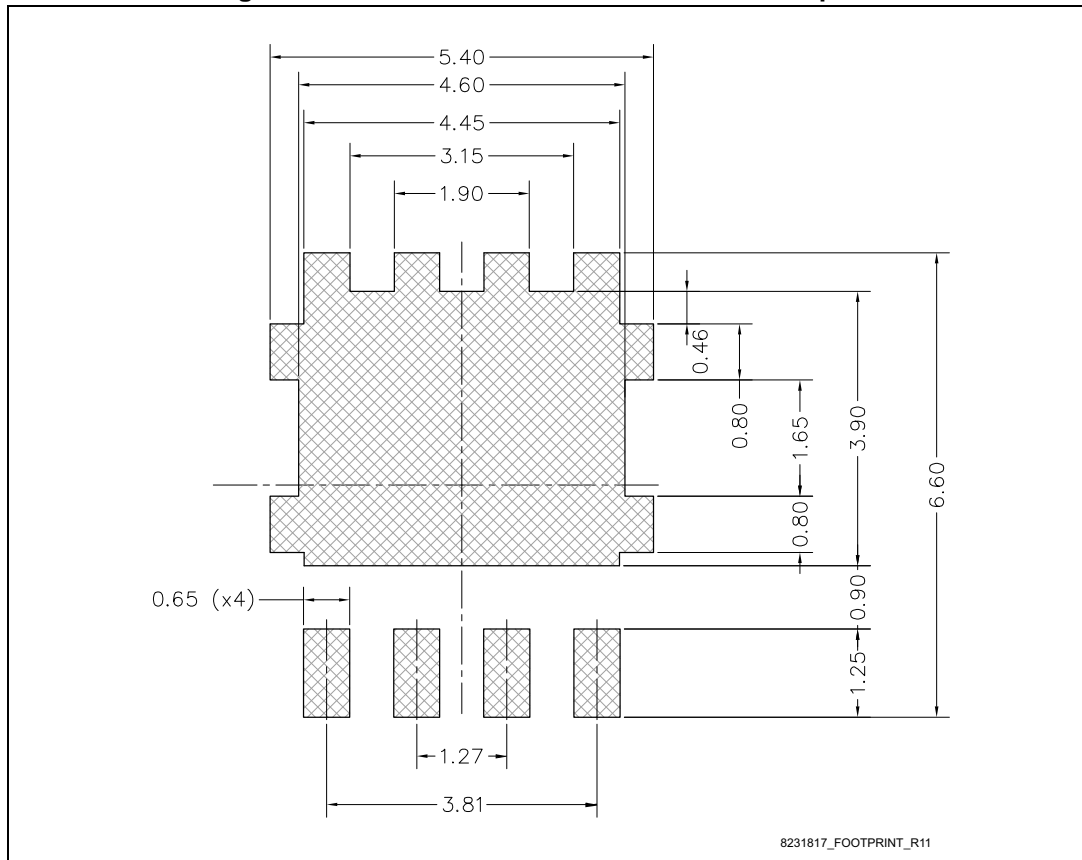


Table 8. PowerFLAT™ 5x6 WF type R mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.80		1.00
A1	0.02		0.05
A2		0.25	
b	0.30		0.50
D	5.00	5.20	5.40
E	6.20	6.40	6.60
D2	4.15		4.45
E2	3.50		3.70
e		1.27	
L	0.70		0.90
L1		0.275	
K	1.275		1.575
E3	2.35		2.55
E4	0.40		0.60
E5	0.08		0.28

Figure 20. PowerFLAT™ 5x6 recommended footprint



4.2 PowerFLAT™ 5x6 packing information

Figure 21. PowerFLAT™ 5x6 type WF tape^(a)

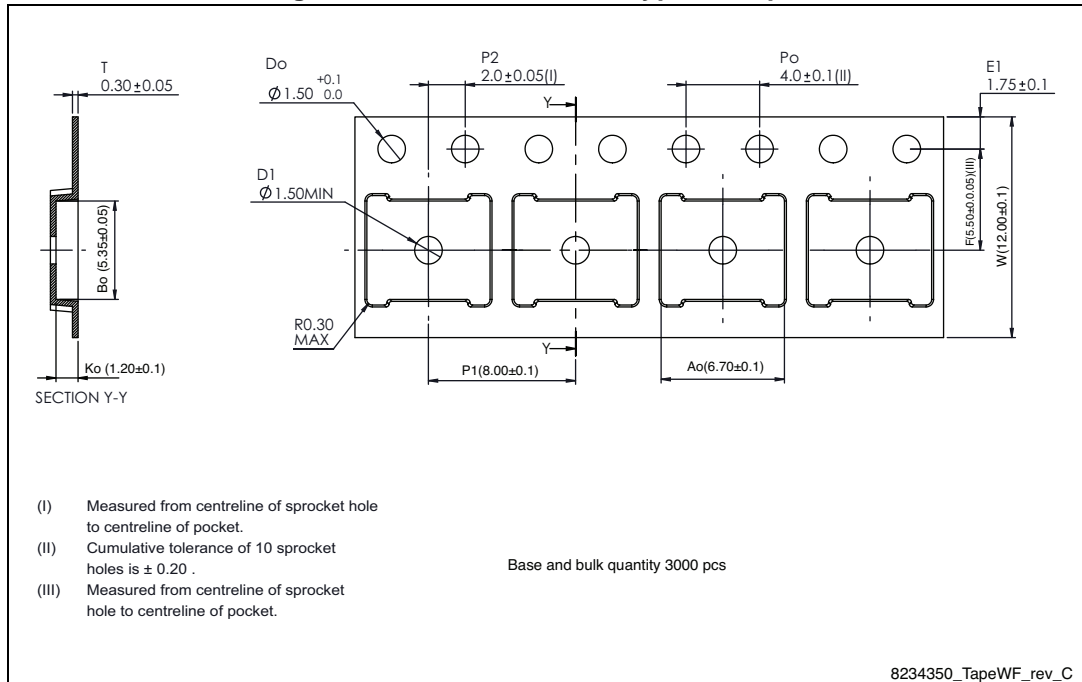
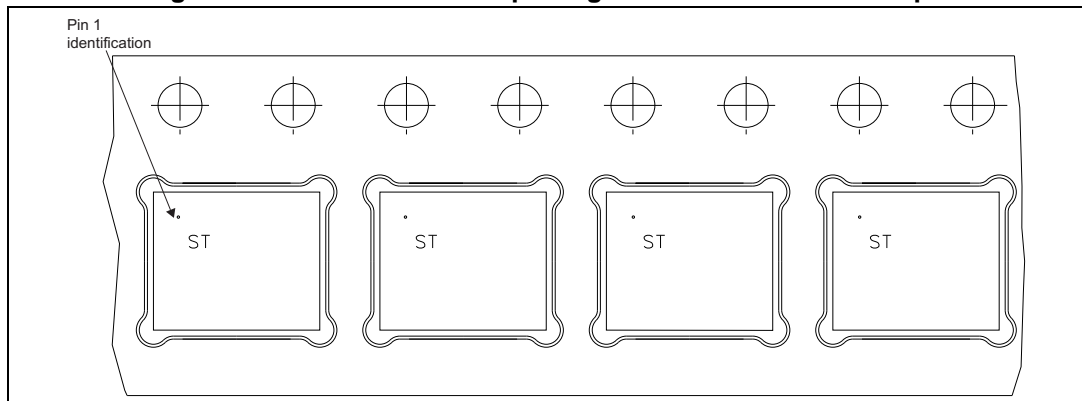
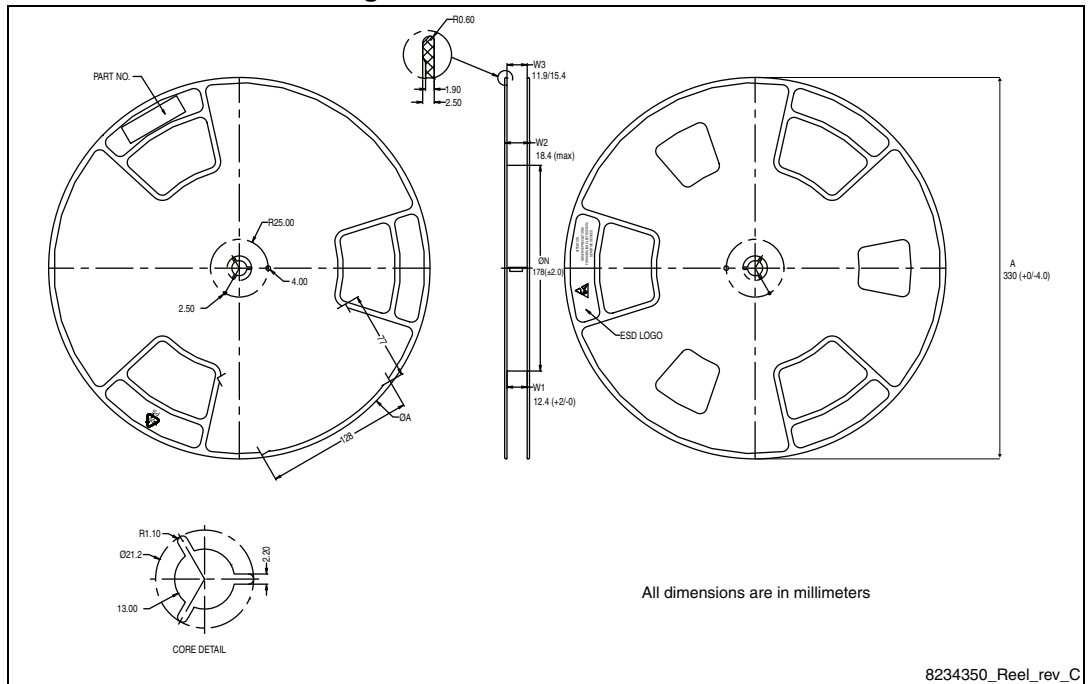


Figure 22. PowerFLAT™ 5x6 package orientation in carrier tape



a. All dimensions are in millimeters.

Figure 23. PowerFLAT™ 5x6 reel



5 Revision history

Table 9. Document revision history

Date	Revision	Changes
16-Oct-2014	1	First release.
12-Oct-2015	2	Updated: Section 4.1: PowerFLAT™ 5x6 WF type R package information Datasheet promoted from preliminary data to production data Minor text changes

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